PROCESS CPD16

Ultra Fast Rectifier

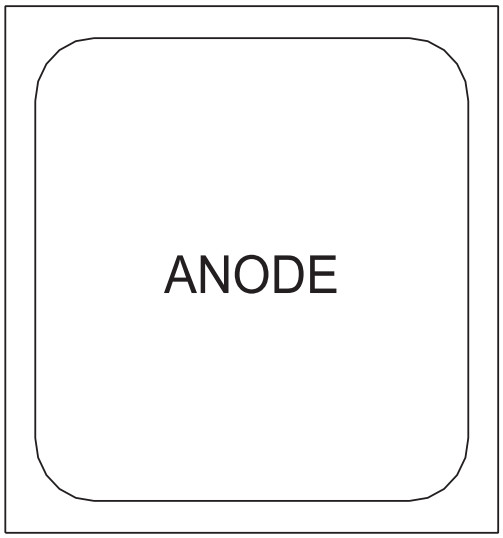
1.0 Amp Glass Passivated Rectifier Chip

Central™
Semiconductor Corp.

PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	50 x 50 MILS
Die Thickness	12.2 MILS
Anode Bonding Pad Area	34 x 34 MILS
Top Side Metalization	Au - 5,000Å
Back Side Metalization	Au - 2,000Å

GEOMETRY



BACKSIDE CATHODE

R0

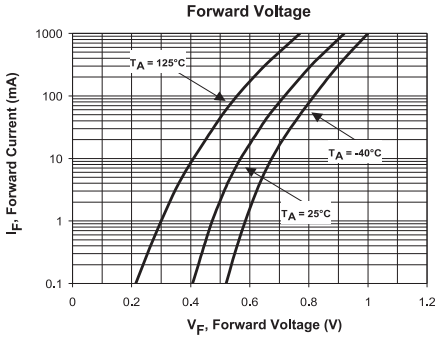
GROSS DIE PER 4 INCH WAFER
4,520

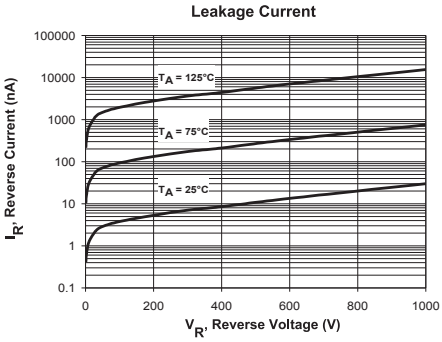
PRINCIPAL DEVICE TYPES
UES1001 thru UES1003
UF4001 thru UF4007
CMR1U-01 Series
CMR1U-01M Series

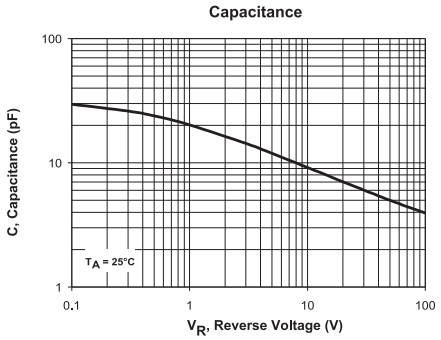
145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

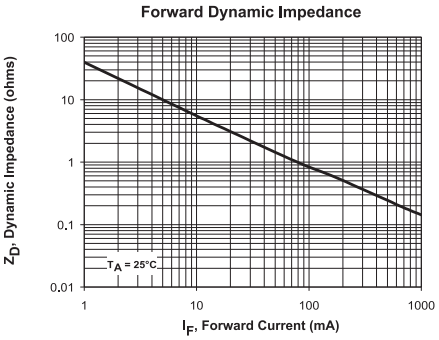
R2 (19-September 2003)

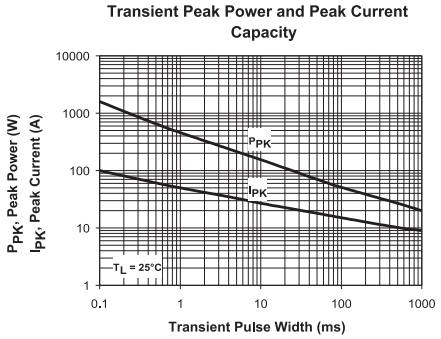
Typical Electrical Characteristics

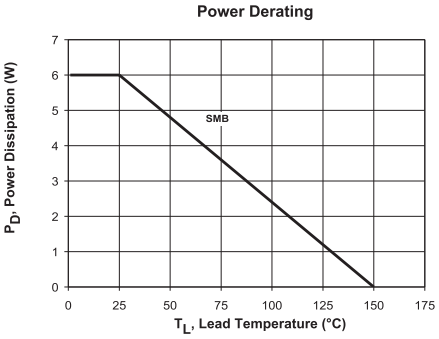












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